

JST25 Series 25A TRIACs

DESCRIPTION:

High current density due to double mesa technology, SIPOS and Glass Passivation.

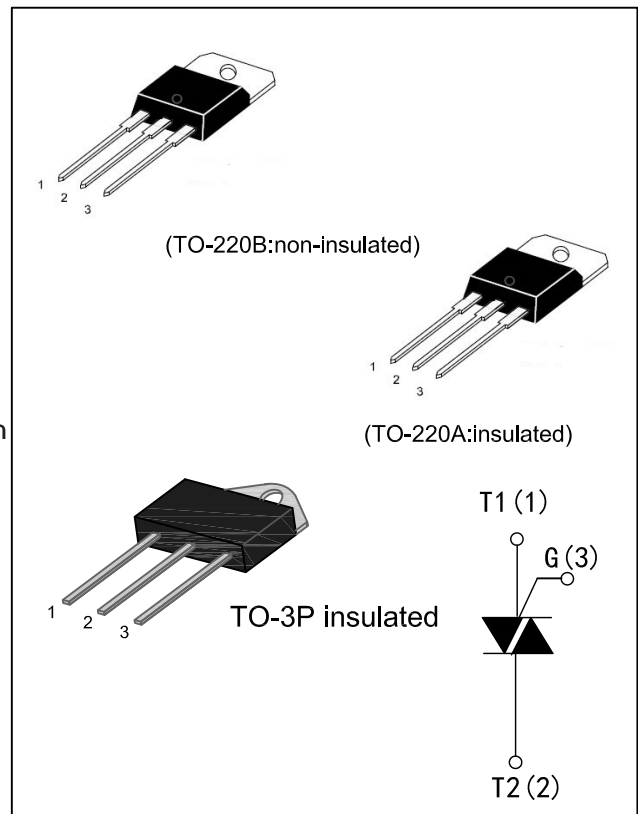
JST25A/JST25B/JST25Z series triacs is suitable for general purpose AC switching, They can be used as an ON/OFF function in applications such as static relays, heating regulation, induction motor starting circuits... or for phase control operation, light dimmers, motor speed controllers.

JST25-CW-BW Series are 3 quadrants triacs, They are specially recommended for use on inductive loads.

JST25A JST25Z series provide a 2500V RMS isolation voltage from all three terminals to external heat sink.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
V_{DRM}/V_{RRM}	600 / 800	V
V_{TM}	1.5	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		Tstg	-40 to +150	°C
Operating junction temperature range		Tj	-40 to +125	°C
Repetitive Peak Off-state Voltage (Tj=25°C) Repetitive Peak Reverse Voltage (Tj=25°C)	JST25x06	VDRM VRRM	600	V
	JST25x08		800	
Non repetitive Surge Peak Off-state Voltage (tp=10ms, Tj=25°C)		VDSM	VDRM+100	V
Non repetitive Peak Reverse Voltage (tp=10ms, Tj=25°C)		VRRM	VRRM+100	
RMS on-state current (full sine wave)	TO-220A Tc=75°C	IT(RMS)	25	A
	TO-220B Tc=100°C			
Non repetitive surge peak on-state current (full cycle, Tj=25°C)	f=60Hz, t=16.7ms	ITSM	260	A
	f=50Hz, t=20ms		250	
I²t Value for fusing	tp=10ms	I²t	340	A²s
Critical rate of rise of on-state current (IG=2×IGT, tr≤100ns, f=120Hz, Tj=125°C)		di/dt	50	A/μs
Peak gate current (tp=20us, Tj=125°C)		IGM	4	A
Peak Gate Power Dissipation (tp=20us, Tj=125°C)		PGM	10	W
Average gate power dissipation (Tj=125°C)		PG(AV)	1	W

ELECTRICAL CHARACTERISTICS(T_j=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant		Limits		Unit
				CW(C)	BW(B)	
I _{GT}	V _D =12V R _L =33Ω	I-II-III	MAX.	35	50	mA
V _{GT}		I-II-III	MAX.	1.3		V
V _{GD}	V _D =V _{DRM} R _L =3.3KΩ T _j =125°C	I-II-III	MIN.	0.2		V
I _L	I _G =1.2I _{GT}	I-III	MAX.	70	80	mA
		II	MAX.	80	100	mA
I _H	I _T =100mA		MAX.	50	75	mA
dV/dt	V _D =67%V _{DRM} gate open T _j =125°C		MIN.	500	1000	V/μs
(di/dt) _c	Without snubber T _j =125°C		MIN.	13	22	A/ms

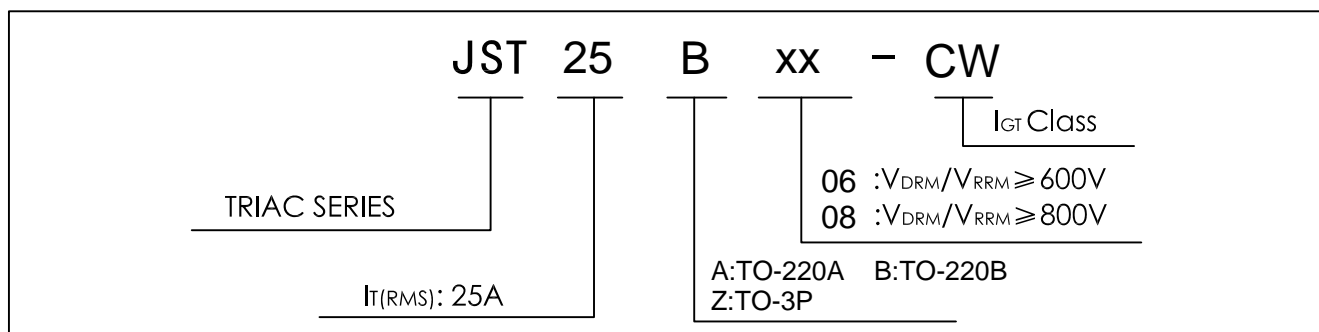
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =35A, t _p =380μs	T _j =25°C	1.5	V
I _{DRM} I _{RRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25°C	5	μA
		T _j =125°C	3	mA

THERMAL RESISTANCES

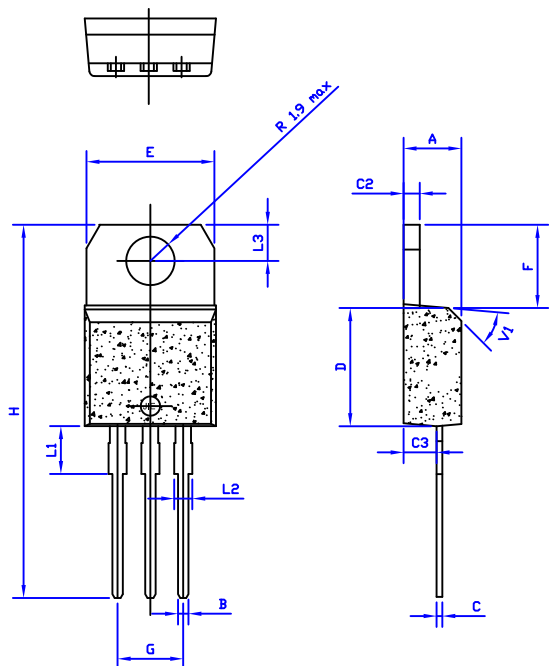
Symbol	Parameter		Value	Unit
R _{th(j-c)}	Junction to Case(AC)	TO-220A	1.7	°C/W
		TO-220B	0.8	
R _{th(j-a)}	Junction to ambient (S=1cm ²)	TO-220A	60	°C/W
		TO-220B	60	

ORDERING INFORMATION



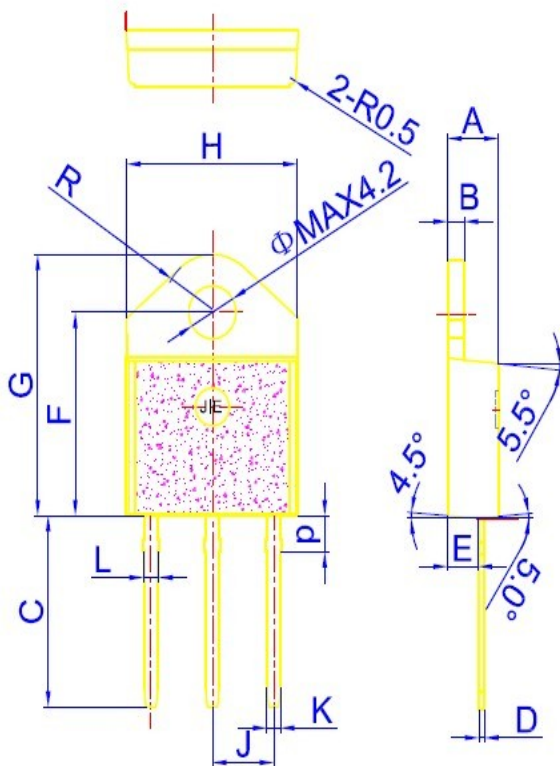
PACKAGE MECHANICAL DATA

TO-220A insulated package and TO-220B non-insulated package



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		1.181
B	0.61		0.88	0.024		0.034
C	0.46		0.70	0.018		0.027
C2	1.23		1.32	0.048		0.051
C3	2.4		2.72	0.094		0.107
D	8.6		9.7	0.338		0.382
E	9.8		10.4	0.386		0.409
F	6.2		6.6	0.244		0.259
G	4.8		5.4	0.189		0.213
H	28.0		29.8	11.0		11.7
L1		3.75			0.147	
L2	1.14		1.7	0.044		0.066
L3	2.65		2.95	0.104		0.116
V1		40°			40°	

TO-3P



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.6	0.565		0.614
D	0.5		0.7	0.020		0.028
E	2.7		2.9	0.106		0.114
F	15.8		16.5	0.622		0.650
G	20.4		21.1	0.815		0.831
H	15.1		15.5	0.594		0.610
J	5.4		5.65	0.213		0.222
K	1.2		1.4	0.047		0.055
L	1.35		1.50	0.053		0.059
P	2.8		3.0	0.110		0.118
R		4.6			0.181	

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

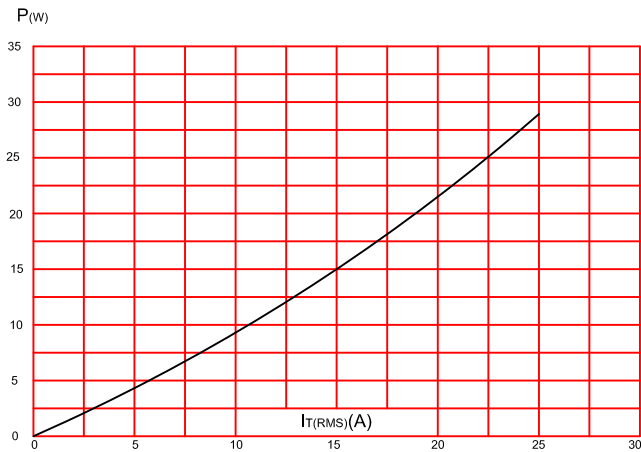


FIG.2: RMS on-state current versus case temperature (full cycle)

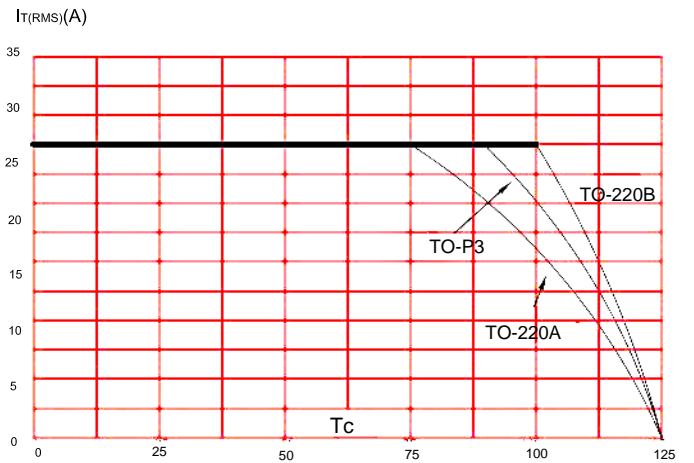


FIG.3: On-state characteristics (maximum values).

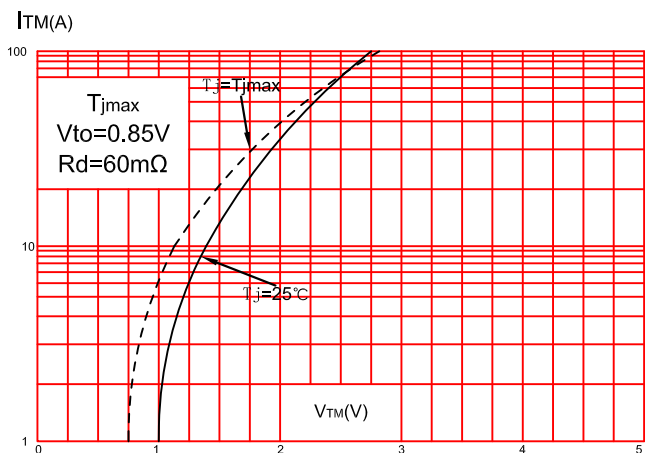


FIG.4: Surge peak on-state current versus number of cycles.

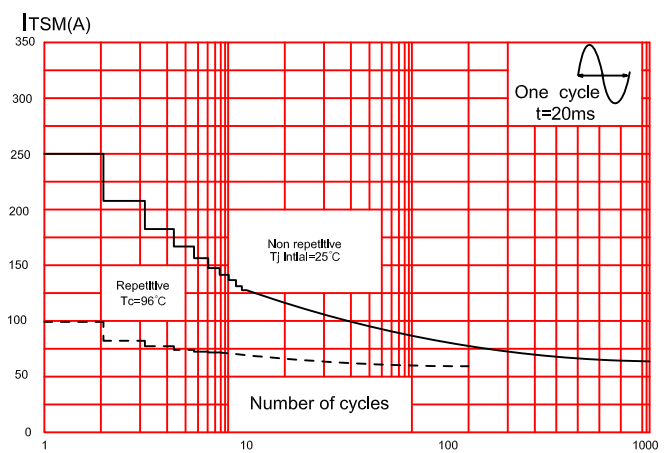


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$, and corresponding value of I^2t .

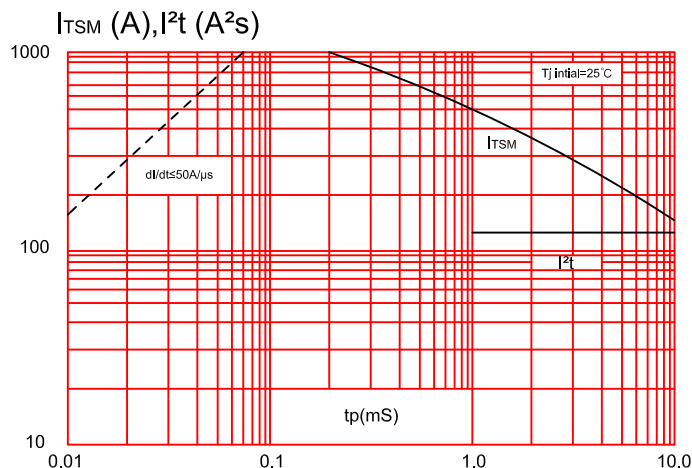


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)

